TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

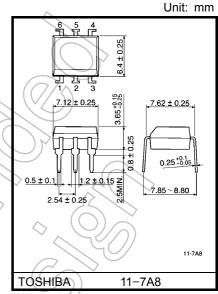
# **TLP371, TLP372**

Office Machine
Household Use Equipment
Telecommunication
Solid State Relay
Programmable Controllers

The TOSHIBA TLP371 and TLP372 consists of a gallium arsenide infrared emitting diode optically coupled to a Darlington connected photo–transistor which has an integrated base–emitter resistor to optimize switching speed and elevated temperature characteristics in a six lead plastic DIP package.

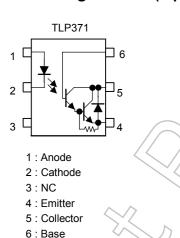
TLP372 has no-base internal connection for high-EMI environments

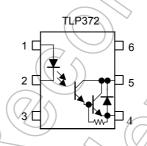
- Current transfer ratio: 1000% (min) (IF = 1mA)
- Isolation voltage: 5000 Vrms (min)
- $\bullet~$  UL recognized: UL1577, file no. E67349



Weight: 0.4 g (typ.)

#### Pin Configurations (top view)





- 1 : Anode
- 2 : Cathode
- 3 : NG
- 4 : Emitter
- 5 : Collector
- 6: NG



#### Absolute Maximum Ratings (Ta = 25°C)

|  | Characteristic                                   | Symbol               | Rating     | Unit    |
|--|--|----------------------|------------|---------|
| Forward current                                      |  | lF                   | 60         | mA      |
| Forward current derating (Ta ≥ 39°C)                 |  | ΔI <sub>F</sub> / °C | -0.7       | mA / °C |
| LED  | Peak forward current (100µs pulse, 100pps)       | I <sub>FP</sub>      | 1          | Α       |
|  | Reverse voltage                                  | V <sub>R</sub>       | 5          | V       |
|  | Junction temperature                             | Tj                   | 125        | ) °C    |
|  | Collector–emitter voltage                        | V <sub>CEO</sub>     | 300        | ٧       |
|  | Collector–base voltage (TLP371)                  | V <sub>CBO</sub>     | 300        | ٧       |
|  | Emitter–collector voltage                        | V <sub>ECO</sub>     | 0.3        | V       |
| Detector   | Emitter-base voltage (TLP371)                    | V <sub>EBO</sub>     |            | ٧       |
| Dete   | Collector current                                | Ic                   | 150        | mA      |
|  | Power dissipation                                | PC                   | 300        | mW      |
|  | Power dissipation derating (Ta ≥ 25°C)           | ΔP <sub>C</sub> / °C | -3.0       | mW/°C   |
|  | Junction temperature                             | Ţ <sub>j</sub>       | 125        | /°C)    |
| Stor   | age temperature range                            | T <sub>stg</sub>     | -55 to 125 | ~ C     |
| Оре  | rating temperature range                         | Topr                 | -55 to 100 | °C      |
| Lead   | d soldering temperature (10 s)                   | T <sub>sol</sub>     | 260        | °C      |
| Tota   | al package power dissipation                     | P <sub>T</sub>       | 350        | mW      |
| Total package power dissipation derating (Ta ≥ 25°C) |  | ΔP <sub>T</sub> / °C | -3.5       | mW / °C |
| Isola  | ation voltage (AC, 1minute, R.H. ≤ 60%) (Note 1) | BVS                  | 5000       | Vrms    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4,5 and 6 shorted together.

#### **Recommended Operating Conditions**

| Characteristic        | Symbol           | Min | Тур. | Max | Unit |
|-----------------------|------------------|-----|------|-----|------|
| Supply voltage        | Vcc              | _   | _    | 200 | V    |
| Forward current       | \ IF             | _   | 16   | 25  | mA   |
| Collector current     | l <sub>C</sub>   | _   | _    | 120 | mA   |
| Operating temperature | T <sub>opr</sub> | -25 | 1    | 85  | °C   |

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

## Individual Electrical Characteristics (Ta = 25°C)

|          | Characteristic                            | Symbol                | Test Condition   | Min      | Тур. | Max | Unit |
|----------|---|-----------------------|--|----------|------|-----|------|
|          | Forward voltage                           | V <sub>F</sub>        | I <sub>F</sub> = 10 mA   | 1.0      | 1.15 | 1.3 | V    |
| LED      | Reverse current                           | I <sub>R</sub>        | V <sub>R</sub> = 5 V   | _        | _    | 10  | μΑ   |
|          | Capacitance                               | C <sub>T</sub>        | V = 0, f = 1 MHz   |          | 30   | _   | pF   |
|          | Collector–emitter breakdown voltage       | V <sub>(BR)</sub> CEO | I <sub>C</sub> = 0.1 mA  | 300      | · –  | _   | V    |
|          | Emitter–collector breakdown voltage       | V <sub>(BR)</sub> ECO | I <sub>E</sub> = 0.1 mA  | 0.3      | ı    | ı   | V    |
|          | Collector–base breakdown voltage (TLP371) | V <sub>(BR)</sub> CBO | I <sub>C</sub> = 0.1 mA  | 300      | ı    | ı   | V    |
|          | Emitter-base breakdown voltage (TLP371)   | V <sub>(BR)</sub> EBO | I <sub>E</sub> = 0.1 mA  | 7        | 1    | 1   | ٧    |
| Detector |   | I <sub>CEO</sub>      | V <sub>CE</sub> = 200 V  | - <      | 10   | 200 | nA   |
| Dete     | Collector dark current                    |                       | V <sub>CE</sub> = 200 V<br>Ta = 85 °C                            | 1        |      | 20  | μΑ   |
|          | Collector dark current (TLP371)           | ICER                  | V <sub>CE</sub> = 200 V<br>Ta = 85 °C<br>R <sub>BE</sub> = 10 MΩ |          | 0.5  | 10  | μΑ   |
|          | Collector dark current (TLP371)           | ICBO                  | V <sub>CE</sub> = 200 V  | 7        | 0.1  | _   | nA   |
|          | DC forward current gain (TLP371)          | h <sub>FE</sub>       | V <sub>CE</sub> = 5 V,<br>I <sub>C</sub> = 10 mA                 | <u> </u> | 7000 | -   | _    |
|          | Capacitance (collector to emitter)        | CCE                   | V = 0, f = 1 MHz   | _        | 10   | _   | pF   |

## Coupled Electrical Characteristics (Ta = 25°C)

| Characteristic                       | Symbol                | Test Condition                                  | MIn  | Тур. | Max | Unit |
|--------------------------------------|-----------------------|---|------|------|-----|------|
| Current transfer ratio               | lc) l <sub>F</sub>    | I <sub>F</sub> = 1 mA, V <sub>CE</sub> = 1 V    | 1000 | 4000 | _   | %    |
| Saturated CTR                        | IC / IF (sat)         | I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 1 V   | 500  | _    | _   | %    |
| Base photo-current (TLP371)          | )) I <sub>PB</sub>    | I <sub>F</sub> = 1 mA, V <sub>CB</sub> = 1 V    | -    | 6    | _   | μΑ   |
| Collector-emitter saturation voltage | V <sub>CE</sub> (sat) | I <sub>C</sub> = 10 mA, I <sub>F</sub> = 1 mA   | -    | _    | 1.0 | V    |
|                                      |                       | I <sub>C</sub> = 100 mA, I <sub>F</sub> = 10 mA | 0.3  | _    | 1.2 | V    |



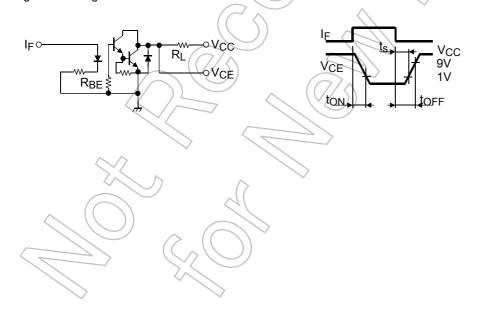
### Isolation Characteristics (Ta = 25°C)

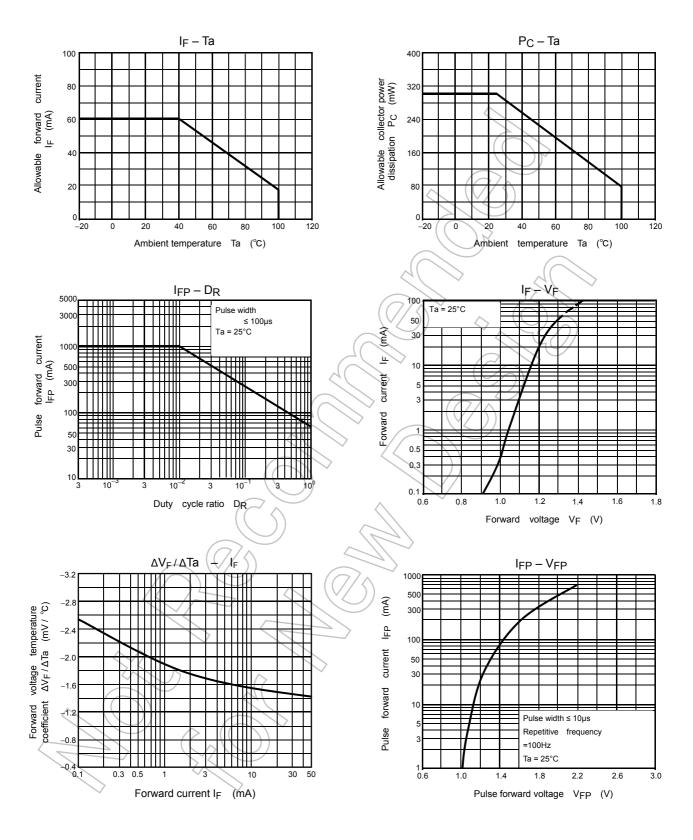
| Characteristic                   | Symbol         | Test Condition                | Min                | Тур.             | Max | Unit                                  |
|----------------------------------|----------------|-------------------------------|--------------------|------------------|-----|---------------------------------------|
| Capacitance<br>(input to output) | CS             | V <sub>S</sub> = 0, f = 1 MHz | _                  | 0.8              | _   | pF                                    |
| Isolation resistance             | R <sub>S</sub> | V <sub>S</sub> = 500 V        | 5×10 <sup>10</sup> | 10 <sup>14</sup> | _   | Ω                                     |
|                                  | BVS            | AC, 1 minute                  | 5000               | _                | _   | \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ |
| Isolation voltage                |                | AC, 1 second, in oil          |                    | 10000            | _   | V <sub>rms</sub>                      |
|                                  |                | DC, 1 minute, in oil          |                    | 10000            | _   | V <sub>dc</sub>                       |

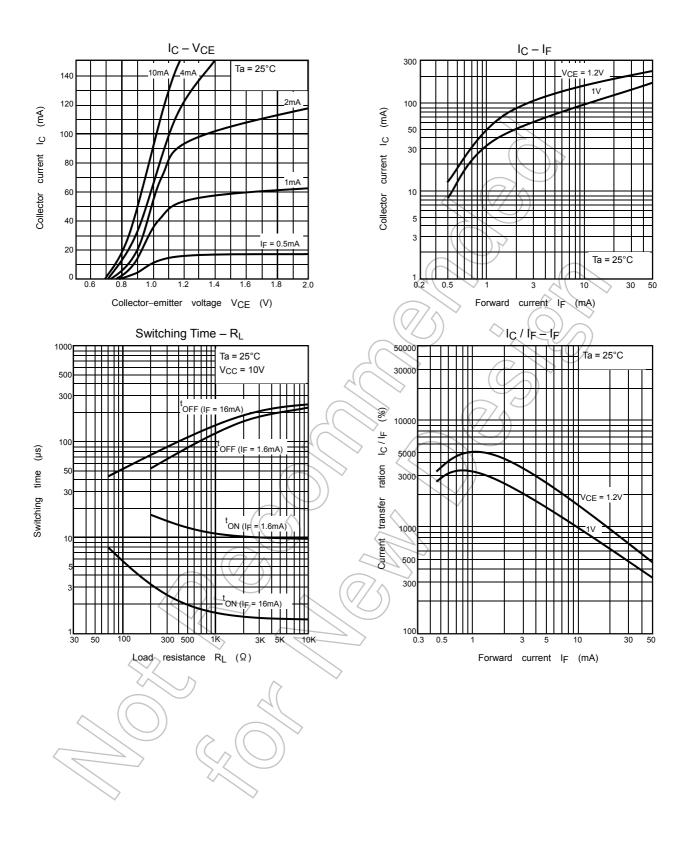
### **Switching Characteristics (Ta = 25°C)**

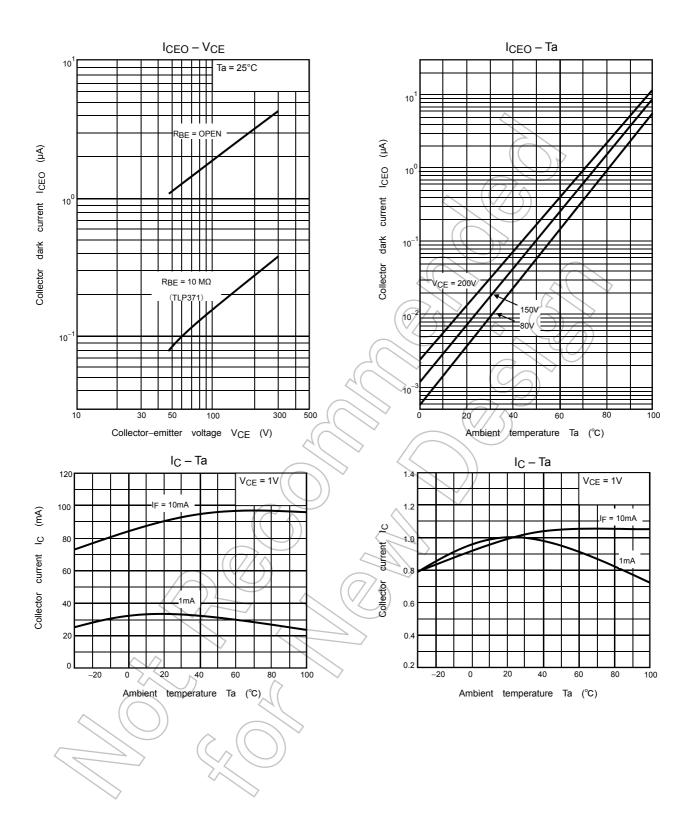
| Characteristic | Symbol           | Test Condition                                  | Min      | Тур. | Max | Unit |
|----------------|------------------|---|----------|------|-----|------|
| Rise time      | t <sub>r</sub>   | $\langle \langle \rangle \rangle$               | _        | 40   | /   |      |
| Fall time      | t <sub>f</sub>   | V <sub>CC</sub> = 10 V                          | - /      | 15   |     |      |
| Turn-on time   | t <sub>on</sub>  | $I_C = 10 \text{ mA}$<br>$R_L = 100\Omega$      | -((      | 50   | < - | μs   |
| Turn-off time  | t <sub>off</sub> |   | K        | (15) | ) — |      |
| Turn-on time   | ton              | $R_L = 180\Omega$ (Fig.1)                       | <u> </u> | 3    | _   |      |
| Storage time   | ts               | RBE = OPEN<br>VCC = 5 V, I <sub>F</sub> = 16 mA |          | 45   | _   | μs   |
| Turn-off time  | tOFF             | VCC = 5 V, IF = 16 MA                           |          | 90   | _   |      |
| Turn-on time   | ton              | $R_L = 180\Omega$ (Fig.1)                       | ) —      | 5    | _   |      |
| Storage time   | t <sub>s</sub>   | $R_{BF} = 10 M\Omega(TLP371)$                   | _        | 40   | _   | μs   |
| Turn-off time  | toff             | V <sub>CC</sub> = 10 V, I <sub>F</sub> = 16 mA  | _        | 80   | _   |      |

Fig.1: Switching time test circuit









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